

SiC

Silicon Carbide Diode

5th Generation thinQ!™

650V SiC Schottky Diode

IDL08G65C5

Final Data Sheet

Rev2.1, 2016-04-19

Power Management & Multimarket

5th Generation thinQ!™ SiC Schottky Diode

1 Description

ThinQ!™ Generation 5 represents Infineon leading edge technology for the SiC Schottky Barrier diodes. The Infineon proprietary diffusion soldering process, already introduced with G3 is now combined with a new, more compact design and thin-wafer technology. The result is a new family of products showing improved efficiency over all load conditions, resulting from both the improved thermal characteristics and a lower figure of merit ($Q_C \times V_f$).

The new thinQ!™ Generation 5 has been designed to complement our 650V CoolMOS™ families: this ensures meeting the most stringent application requirements in this voltage range.

Features

- Revolutionary semiconductor material - Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Breakdown voltage tested at 18 mA²⁾
- Optimized for high temperature operation

Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI

Applications

- Switch mode power supply
- Power factor correction
- Solar inverter
- Uninterruptible power supply

Table 1 Key Performance Parameters

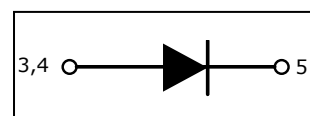
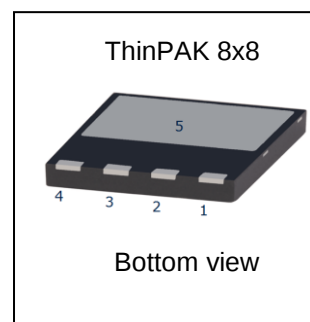
Parameter	Value	Unit
V_{DC}	650	V
$Q_C; V_R=400V$	13	nC
$E_C; V_R=400V$	2.9	μJ
$I_F @ T_C < 150^\circ C$	8	A

Table 2 Pin Definition

Pin 1	Pin 2	Pin 3	Pin 4	Pin 5
n.c.	n.c.	A	A	C

Type / ordering Code	Package	Marking
IDL08G65C5	PG-VSON-4	D0865C5

IDL08G65C5



Related Links

- <http://www.infineon.com/sic>
- [ThinPAK Webpage](#)
- [ThinPAK Application Note](#)

1) J-STD20 and JESD22

2) All devices tested under avalanche conditions for a time periode of 10ms

Table of Contents

1	Description.....	2
2	Maximum ratings.....	4
3	Thermal characteristics.....	4
4	Electrical characteristics.....	5
5	Electrical characteristics diagrams.....	6
6	Simplified Forward Characteristics Model	8
7	Package outlines	9
8	Revision History	10

2 Maximum ratings

Table 3 Maximum ratings

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Continuous forward current	I_F	—	—	8	A	$T_C < 125^\circ\text{C}$, $D=1$
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	—	—	43		$T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$
		—	—	36		$T_C = 150^\circ\text{C}$, $t_p=10\text{ ms}$
Non-repetitive peak forward current	$I_{F,max}$	—	—	364		$T_C = 25^\circ\text{C}$, $t_p=10\text{ }\mu\text{s}$
i^2t value	$\int i^2 dt$	—	—	9.5	A^2s	$T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$
		—	—	6.4		$T_C = 150^\circ\text{C}$, $t_p=10\text{ ms}$
Repetitive peak reverse voltage	V_{RRM}	—	—	650	V	$T_j = 25^\circ\text{C}$
Diode dv/dt ruggedness	dv/dt	—	—	100	V/ns	$V_R=0..480\text{ V}$
Power dissipation	P_{tot}	—	—	96	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	$T_j; T_{stg}$	-55	—	150	$^\circ\text{C}$	

3 Thermal characteristics

Table 4 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction-case	R_{thJC}	—	1.0	1.3	K/W	SMD version, device on PCB, 6cm ² cooling area ¹⁾
Thermal resistance, junction-ambient	R_{thJA}	—	—	45		

1) Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70μm) for drain connection. PCB is vertical without air stream cooling.

4 Electrical characteristics

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	650	–	–	V	$I_R = 0.14 \text{ mA}$, $T_j = 25^\circ\text{C}$
Diode forward voltage	V_F	–	1.5	1.7		$I_F = 8 \text{ A}$, $T_j = 25^\circ\text{C}$
		–	1.8	2.1		$I_F = 8 \text{ A}$, $T_j = 150^\circ\text{C}$
Reverse current	I_R	–	0.4	140	μA	$V_R = 650 \text{ V}$, $T_j = 25^\circ\text{C}$
		–	0.1	50		$V_R = 600 \text{ V}$, $T_j = 25^\circ\text{C}$
		–	1.6	1000		$V_R = 650 \text{ V}$, $T_j = 150^\circ\text{C}$

Table 6 AC characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Total capacitive charge	Q_c	–	13		nC	$V_R = 400 \text{ V}$, $di/dt = 200 \text{ A}/\mu\text{s}$, $I_F \leq I_{F, \text{MAX}}$, $T_j = 150^\circ\text{C}$.
Total Capacitance	C	–	250	–	pF	$V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$
		–	32	–		$V_R = 300 \text{ V}$, $f = 1 \text{ MHz}$
		–	32	–		$V_R = 600 \text{ V}$, $f = 1 \text{ MHz}$

5 Electrical characteristics diagrams

Table 7

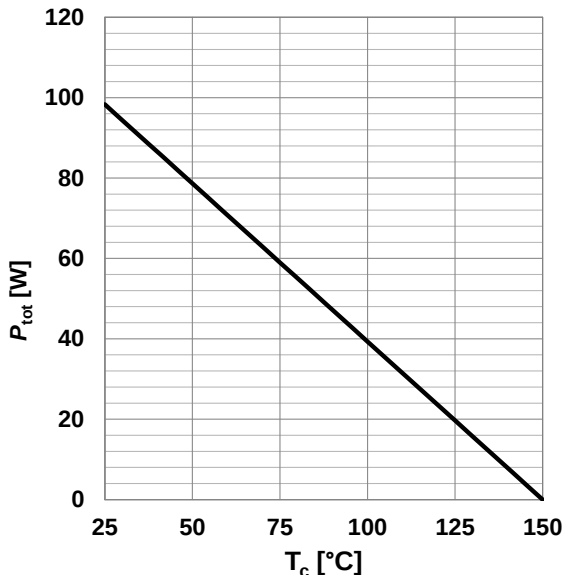
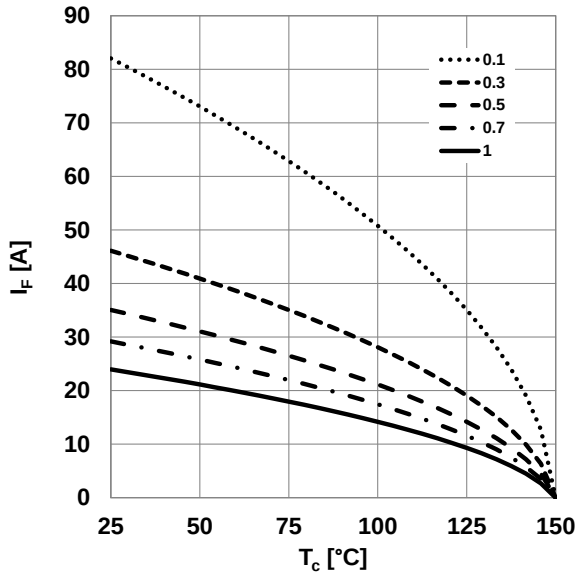
Power dissipation	Maximal diode forward current
	
$P_{\text{tot}} = f(T_c); R_{\text{thJC,max}}$	$I_F = f(T_c); R_{\text{thJC,max}}; T_j \leq 150^\circ\text{C}; \text{parameter } D = \text{duty cycle}$

Table 8

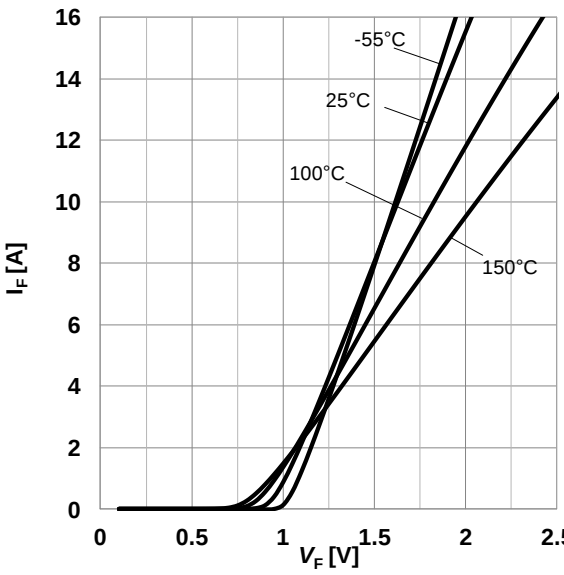
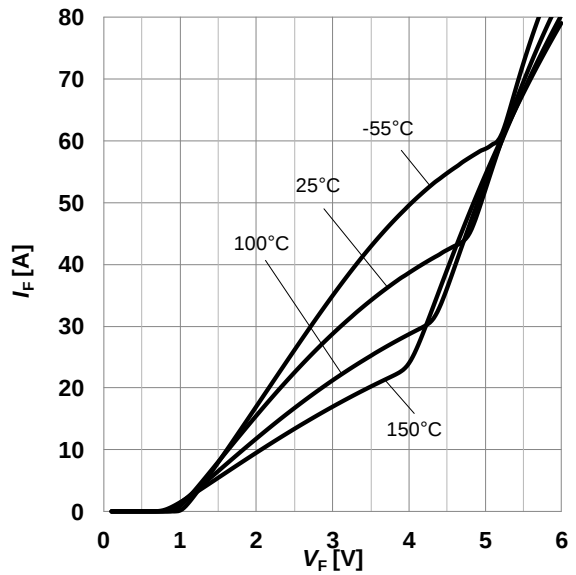
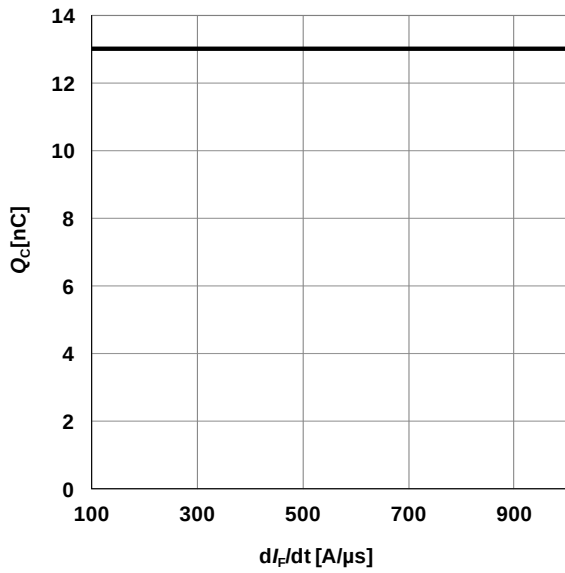
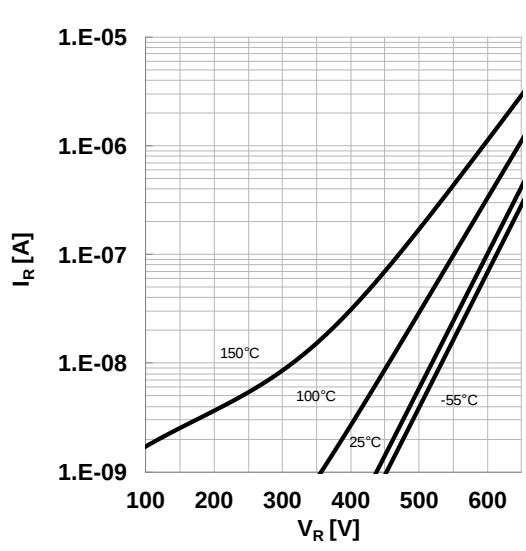
Typical forward characteristics	Typical forward characteristics in surge current
	
$I_F = f(V_F); t_p = 200 \mu\text{s}; \text{parameter: } T_j$	$I_F = f(V_F); t_p = 200 \mu\text{s}; \text{parameter: } T_j$

Table 9

Typ. capacitance charge vs. current slope ¹⁾	Typ. reverse current vs. reverse voltage
	
$Q_C = f(dI_F/dt); T_J = 150^\circ\text{C}; V_R = 400\text{ V}; I_F \leq I_{F,\text{max}}$	$I_R = f(V_R); \text{parameter: } T_J;$

1) Only capacitive charge, guaranteed by design.

Table 10

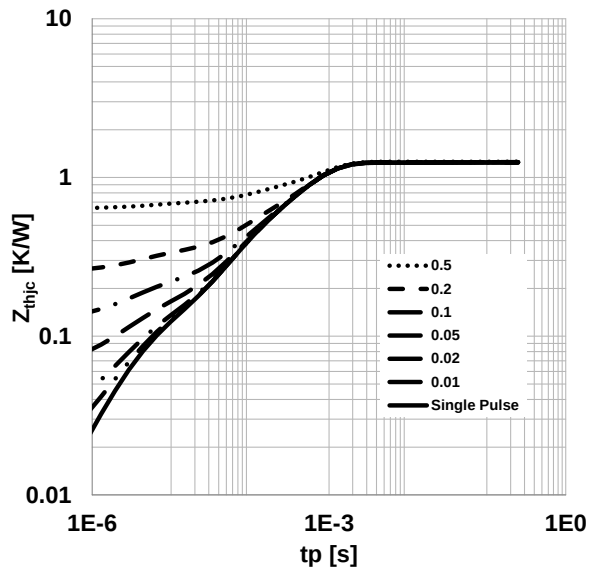
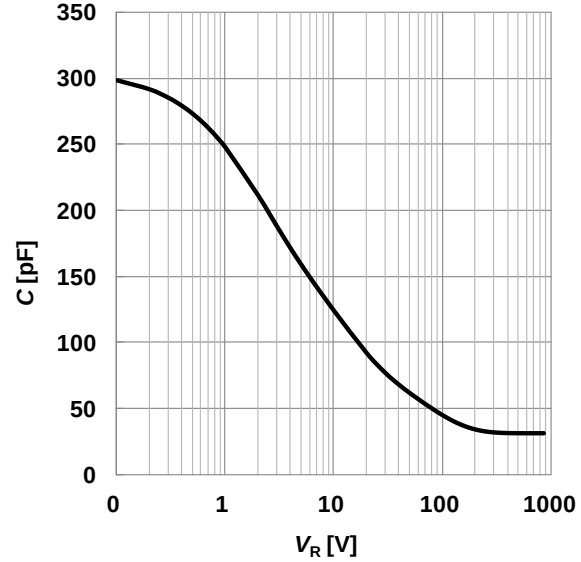
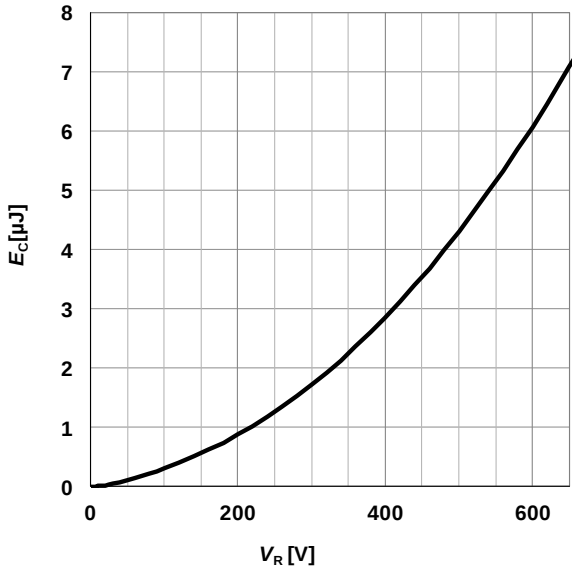
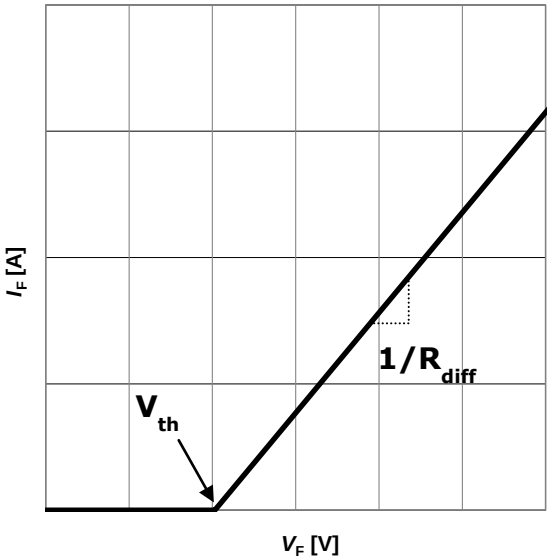
Max. transient thermal impedance	Typ. capacitance vs. reverse voltage
	
$Z_{th,jc} = f(t_p); \text{parameter: } D = t_p/T$	$C = f(V_R); T_J = 25^\circ\text{C}; f = 1\text{ MHz}$

Table 11

Typ. capacitance stored energy
 $E_C = f(V_R)$

6 Simplified Forward Characteristics Model

Table 12

Equivalent forward current curve	Mathematical Equation
 $V_F = f(I_F)$	$V_F = V_{TH} + R_{DIFF} \cdot I_F$ $V_{TH}(T_j) = -0.001 \cdot T_j + 1.04 \text{ [V]}$ $R_{DIFF}(T_j) = 1.6 \cdot 10^{-6} \cdot T_j^2 + 1.6 \cdot 10^{-4} \cdot T_j + 0.058 \text{ [}\Omega\text{]}$
	T_j in °C; $-55^\circ\text{C} < T_j < 150^\circ\text{C}$; $I_F < 16 \text{ A}$

7 Package outlines

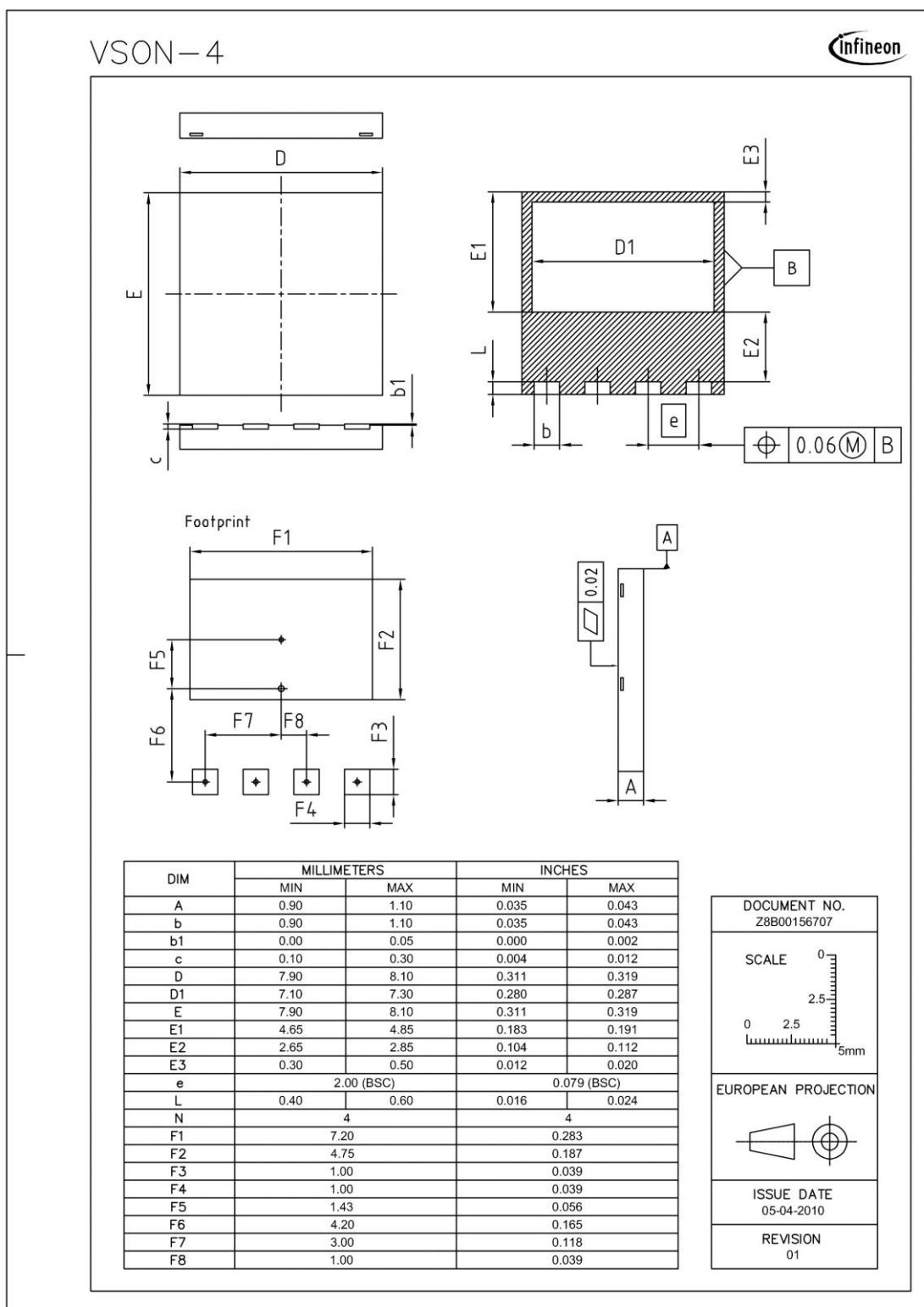


Figure 1 Outlines ThinPAK 8x8, dimensions in mm/inches

8 Revision History

5th Generation thinQ!™ SiC Schottky Diode

Revision History: 2016-04-19, Rev. 2.1

Previous Revision:

Revision	Subjects (major changes since last version)
2.0	Release of the final datasheet
2.1	Correction of Test Condition Diode Forward Voltage

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